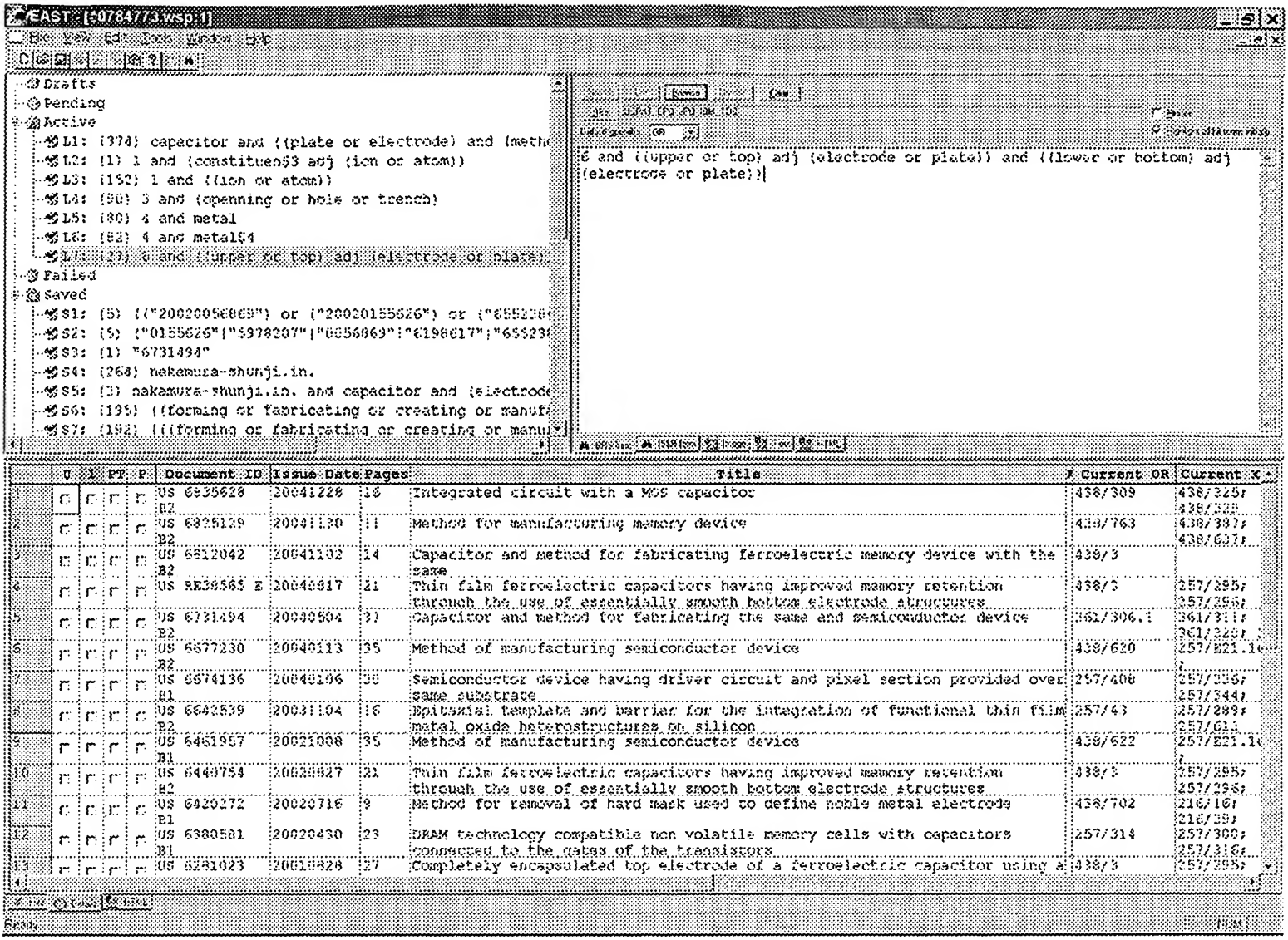

	U	I	PT	P	Document ID	Issue Date	Pages	Title	Current OR	Current X
1	☐	☐	☐	☐	US 6835620 B2	20041228	16	Integrated circuit with a MOS capacitor	438/309	438/325; 438/328
2	☐	☐	☐	☐	US 6825129 B2	20041130	11	Method for manufacturing memory device	438/763	438/387; 438/637;
3	☐	☐	☐	☐	US 6812042 B2	20041102	14	Capacitor and method for fabricating ferroelectric memory device with the same	438/3	
4	☐	☐	☐	☐	US RE38565 E	20040817	21	Thin film ferroelectric capacitors having improved memory retention through the use of essentially smooth bottom electrode structures	438/3	257/295; 257/296;
5	☐	☐	☐	☐	US 6731494 B2	20040504	37	Capacitor and method for fabricating the same and semiconductor device	361/306.1	361/311; 361/320;
6	☐	☐	☐	☐	US 6677230 B2	20040113	35	Method of manufacturing semiconductor device	438/620	257/E21.1
7	☐	☐	☐	☐	US 6674136 B1	20040106	38	Semiconductor device having driver circuit and pixel section provided over same substrate	257/408	257/336; 257/344;
8	☐	☐	☐	☐	US 6663539 B2	20031104	16	Epitaxial template and barrier for the integration of functional thin film metal oxide heterostructures on silicon	257/43	257/289; 257/611
9	☐	☐	☐	☐	US 6461957 B1	20021008	35	Method of manufacturing semiconductor device	438/622	257/E21.1
10	☐	☐	☐	☐	US 6440754 B2	20020827	21	Thin film ferroelectric capacitors having improved memory retention through the use of essentially smooth bottom electrode structures	438/3	257/295; 257/296;
11	☐	☐	☐	☐	US 6420272 B1	20020716	9	Method for removal of hard mask used to define noble metal electrode	438/702	216/16; 216/39;
12	☐	☐	☐	☐	US 6380581 B1	20020430	23	DRAM technology compatible non volatile memory cells with capacitors connected to the gates of the transistors	257/314	257/300; 257/316;
13	☐	☐	☐	☐	US 6281023	20010828	27	Completely encapsulated top electrode of a ferroelectric capacitor using a	438/3	257/295;